

## INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.2204-01	Appln. No.	10/775065
Applicant	Yuuichi MIKATA et al.		
Filing Date	Herewith 2-11-04	Group:	2813

U.S. PATENT DOCUMENTS						
Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
AL	5,786,027	Jul. 28, 1998	Rolfson			
AL	5,767,004	Jun. 16, 1998	Balasubramanian et al.			
AL	5,753,134	May 19, 1998	Biebl			
AL	5,354,702	Oct. 11, 1994	Arima et al.			
AL	4,745,088	May 17, 1988	Inoue et al.			
AL	5,150,178	Sep. 1992	Mori			
AL	4,295,265	Oct. 1981	Horiuchi et al.			
AL	5,759,883	Jun. 1998	Kinoshita			
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AL	4,745,079	May 1988	Pfiester			
AL	5,360,756	Nov. 1994	Tamura			
AL	5,831,694	Nov. 1998	Onisawa et al.			
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AL	5,999,236	Dec. 1999	Nakajima et al.			
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AL	6,118,140	Sep. 2000	Nakamima et al.			

Examiner	Harvea Schulz	Date Considered	4/15/05
*Examiner:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		
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FOREIGN PATENT DOCUMENTS						
	Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
<i>Re</i>	03163874	Jul. 15, 1991	Japan	—	—	English Abstract
<i>Re</i>	9-246206	Sep. 19, 1997	Japan	—	—	English Abstract
<i>Re</i>	63042174	Feb. 23, 1988	Japan	—	—	English Abstract
<i>Re</i>	08321612	Dec. 3, 1996	Japan	—	—	English Abstract
<i>Re</i>	3-62-033470	Feb. 1987	Japan	—	—	
<i>Re</i>	3-62-037160	Feb. 1987	Japan	—	—	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
	Copy of European Search Report dated May 22, 2001.
<i>Re</i>	Miura, H. et al., "Effect of Mechanical Stress on Reliability of Gate-Oxide Film in MOS Transistors", INTERNATIONAL ELECTRON DEVICES MEETING, TECHNICAL DIGEST (Cat. No. 96CH35961), San Francisco, CA, pp. 743-746, 12/1996
<i>Re</i>	Hamada et al., A New Aspect on Mechanical Stress Effects in Scaled MOS Devices, 1990, IEEE, Symposium on VLSI Technology, pp. 113-14
<i>Re</i>	Hamada et al., Hot-Electron Trapping Activation Energy in PMOSFET's Under Mechanical Stress, Jan. 1994, IEEE, Electron Device Letters, Vol. 15, No. 1, pp. 31-32.

Examiner	<i>Wesley Schuler</i>	Date Considered	4/15/05
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